



VBO 20

## Single Phase Rectifier Bridge

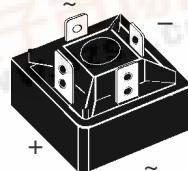
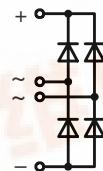
### Standard and Avalanche Types

$V_{RSM}$	$V_{BRmin}^{(1)}$	$V_{RRM}$	Standard Type	Avalanche Type
V	V	V		
900		800	VBO 20-08NO2	
1300	1230	1200	VBO 20-12NO2	VBO 20-12AO2
1500	1430	1400	VBO 20-14NO2	VBO 20-14AO2
1700	1630	1600	VBO 20-16NO2	VBO 20-16AO2

① For Avalanche Types only

$$I_{dAV} = 31 \text{ A}$$

$$V_{RRM} = 800-1600 \text{ V}$$

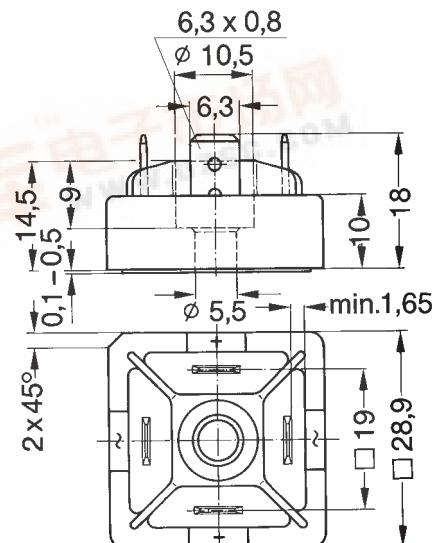


Symbol	Test Conditions		Maximum Ratings			Features
$I_{dAV}$ ②	$T_c = 85^\circ\text{C}$ , module			31	A	Avalanche rated parts available
$I_{dAVM}$	module			40	A	Package with DCB ceramic base plate
$P_{RSM}$	$T_{VJ} = T_{VJM}$	$t = 10 \mu\text{s}$		3.4	kW	Isolation voltage 3600 V~
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C};$ $V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	300	A		Planar passivated chips
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	250	A		Low forward voltage drop
$I^2t$	$T_{VJ} = 45^\circ\text{C}$ $V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	450	$\text{A}^2\text{s}$		$\frac{1}{4}$ " fast-on terminals
	$T_{VJ} = T_{VJM}$ $V_R = 0$	$t = 10 \text{ ms (50 Hz), sine}$ $t = 8.3 \text{ ms (60 Hz), sine}$	312	$\text{A}^2\text{s}$		UL registered E 72873
			290	$\text{A}^2\text{s}$		
$T_{VJ}$			-40...+150		$^\circ\text{C}$	
$T_{VJM}$			150		$^\circ\text{C}$	
$T_{stg}$			-40...+125		$^\circ\text{C}$	
$V_{ISOL}$	50/60 Hz, RMS $I_{ISOL} \leq 1 \text{ mA}$	$t = 1 \text{ min}$ $t = 1 \text{ s}$	3000	V~		
			3600	V~		
$M_d$	Mounting torque (M5) (10-32 UNF)		1.5-2	Nm		
			13-18	lb.in.		
Weight	typ.		15	g		

Symbol	Test Conditions		Characteristic Values		
$I_R$	$V_R = V_{RRM};$ $V_R = V_{RRM};$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = T_{VJM}$	$\leq$	0.3	mA
			$\leq$	5	mA
$V_F$	$I_F = 55 \text{ A};$	$T_{VJ} = 25^\circ\text{C}$	$\leq$	1.6	V
$V_{TO}$	For power-loss calculations only		0.85	V	
$r_T$	$T_{VJ} = T_{VJM}$		14	$\text{m}\Omega$	
$R_{thJC}$	per diode, DC current		3.0	K/W	
	per module		0.75	K/W	
$R_{thJK}$	per diode, DC current		3.4	K/W	
	per module		0.85	K/W	
$d_s$	Creeping distance on surface		13	mm	
$d_a$	Creepage distance in air ③		9.5	mm	
$a$	Max. allowable acceleration		50	$\text{m/s}^2$	

Data according to IEC 60747 and refer to a single diode unless otherwise stated

② for resistive load at bridge output, ③ with isolated fast-on tabs.



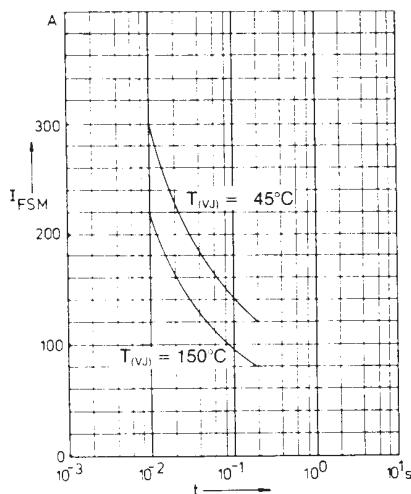


Fig. 1 Surge overload current per diode  
 $I_{FSM}$ : Crest value,  $t$ : duration

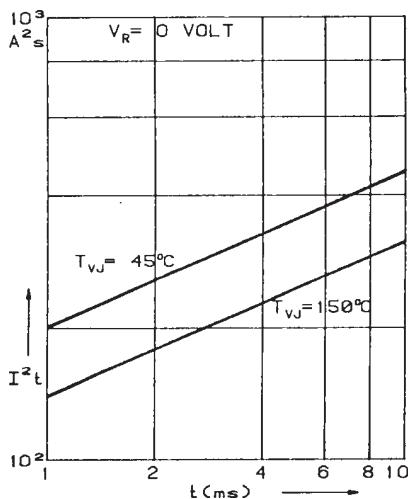


Fig. 2  $I^2t$  versus time (1-10 ms)  
per diode

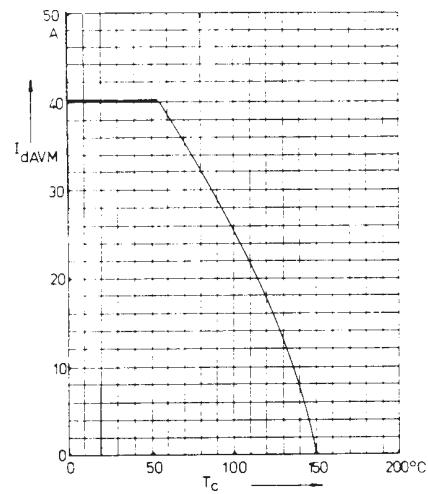


Fig. 3 Max. forward current at case  
temperature

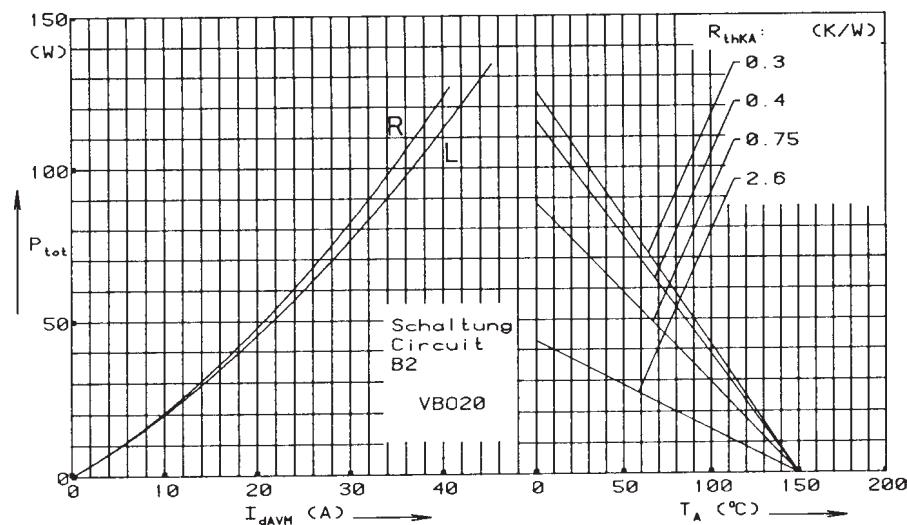


Fig. 4 Power dissipation versus direct output current and ambient temperature

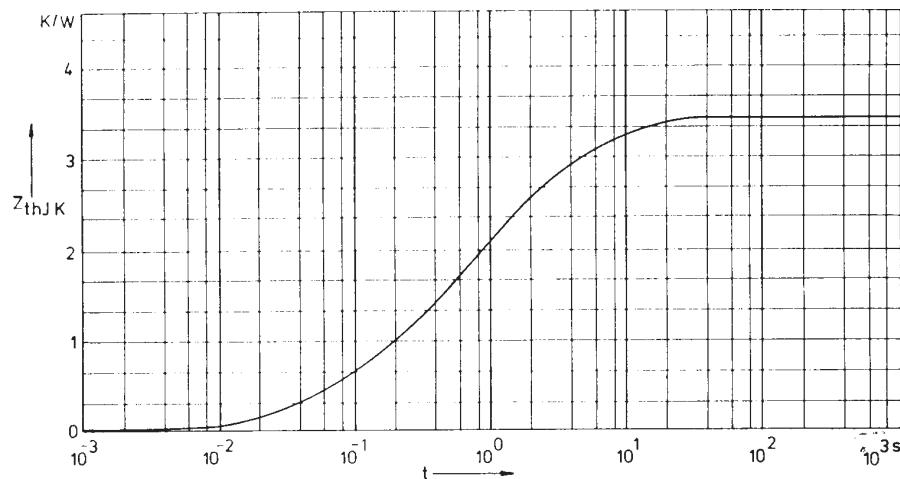


Fig. 5 Transient thermal impedance junction to heatsink per diode

IXYS reserves the right to change limits, test conditions and dimensions.

Constants for  $Z_{thJK}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.775	0.0788
2	1.390	0.504
3	1.255	3.701